

Silicon PNP Power Transistors

KSA1614

DESCRIPTION

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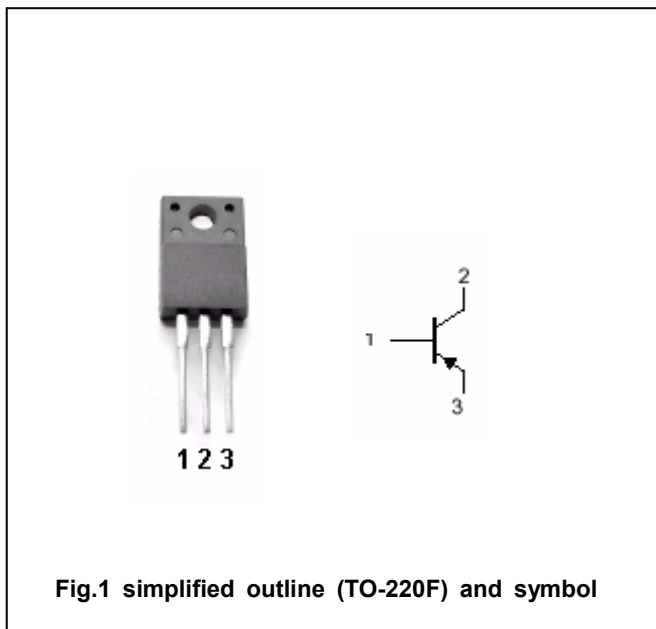
- With TO-220F package
- Collector-base voltage:  $V_{CBO}=-80V$
- Collector dissipation:  $P_C=20W(T_C=25^\circ C)$

APPLICATIONS

- Power regulator
- Low frequency power amplifier

PINNING

PIN	DESCRIPTION
1	Base
2	Collector
3	Emitter



Absolute maximum ratings ( $T_a=25^\circ C$ )

SYMBOL	PARAMETER	CONDITIONS	VALUE	UNIT
$V_{CBO}$	Collector-base voltage	Open emitter	-80	V
$V_{CEO}$	Collector-emitter voltage	Open base	-55	V
$V_{EBO}$	Emitter-base voltage	Open collector	-5	V
$I_C$	Collector current		-3	A
$P_C$	Collector dissipation	$T_C=25^\circ C$	20	W
$T_j$	Junction temperature		150	$^\circ C$
$T_{stg}$	Storage temperature		-55~150	$^\circ C$

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## CHARACTERISTICS

T<sub>j</sub>=25°C unless otherwise specified

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SYMBOL	PARAMETER	CONDITIONS	MIN	TYP.	MAX	UNIT
V <sub>(BR)CEO</sub>	Collector-emitter breakdown voltage	I <sub>C</sub> =-10mA ; I <sub>B</sub> =0	-55			V
V <sub>(BR)CBO</sub>	Collector-base breakdown voltage	I <sub>C</sub> =-500μA ; I <sub>E</sub> =0	-80			V
V <sub>(BR)EBO</sub>	Emitter-base breakdown voltage	I <sub>E</sub> =-500μA ; I <sub>C</sub> =0	-5			V
V <sub>CEsat</sub>	Collector-emitter saturation voltage	I <sub>C</sub> =-1A ; I <sub>B</sub> =-0.1A		-0.15	-0.5	V
I <sub>CBO</sub>	Collector cut-off current	V <sub>CB</sub> =-50V ; I <sub>E</sub> =0			-50	μA
h <sub>FE</sub>	DC current gain	I <sub>C</sub> =-0.5A ; V <sub>CE</sub> =-5V	40		240	

◆ h<sub>FE</sub> Classifications

R	O	Y
40-80	70-140	120-240

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PACKAGE OUTLINE

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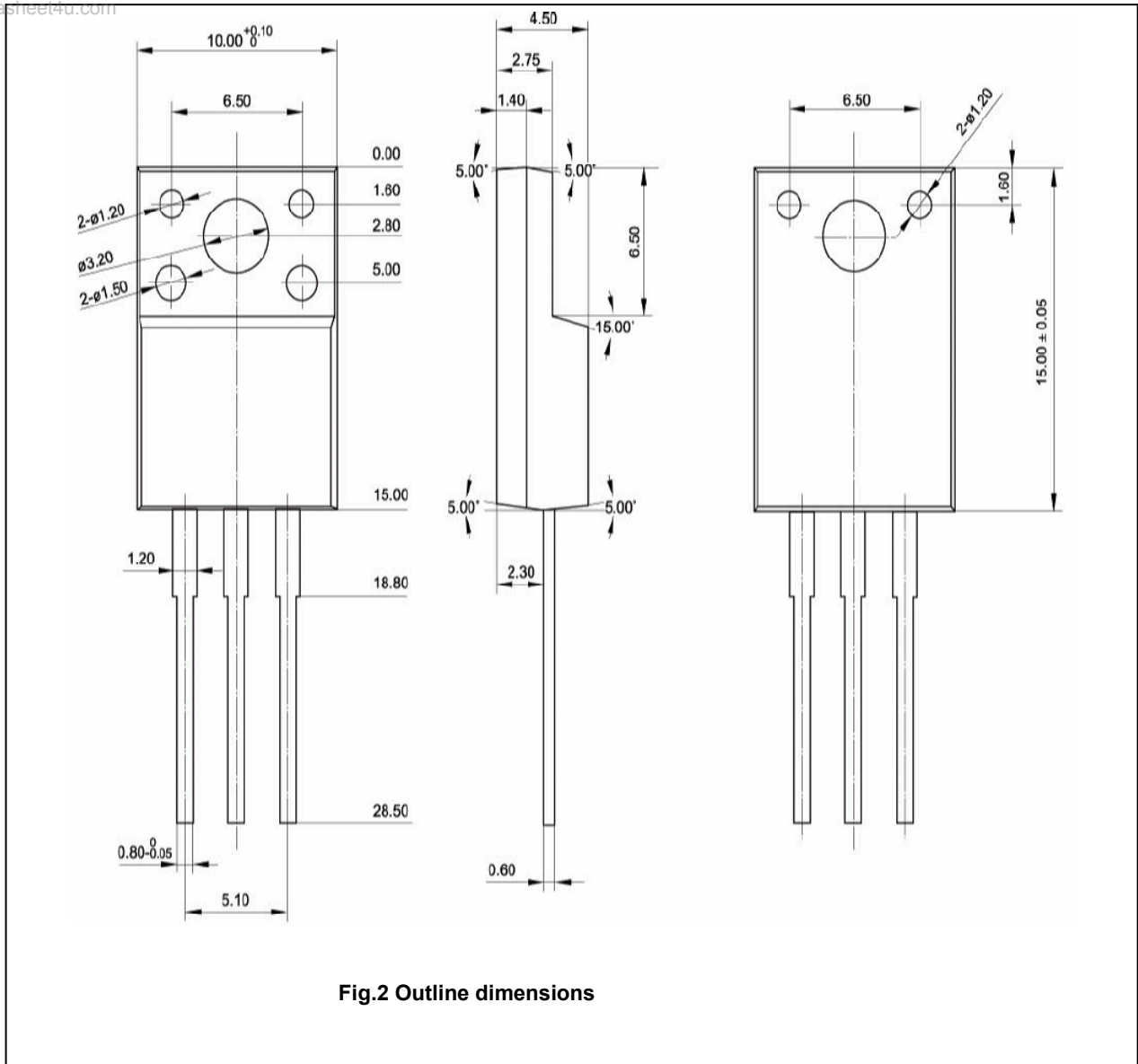


Fig.2 Outline dimensions